

SANYO

No.4665

2SA1838

PNP Epitaxial Planar Silicon Transistor

Muting Circuit Applications

Features

- Very small-sized package permitting 2SA1838-applied sets to be made small and slim.
- Small output capacitance.
- Low collector-to-emitter saturation voltage.
- Low ON resistance.

Absolute Maximum Ratings at Ta = 25°C

			unit
Collector-to-Base Voltage	V_{CBO}	-15	V
Collector-to-Emitter Voltage	V_{CEO}	-10	V
Emitter-to-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-100	mA
Collector Current (Pulse)	I_{CP}	-200	mA
Base Current	I_B	-20	mA
Collector Dissipation	P_C	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

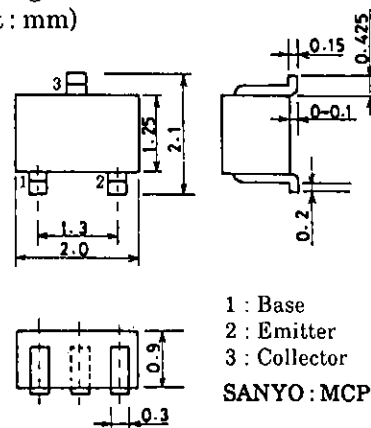
Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = -12V, I_E = 0$			-0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = -2V, I_C = -5mA$	200		600	
Gain-Bandwidth Product	f_T	$V_{CE} = -5V, I_C = -10mA$		600		MHz
Output Capacitance	C_{ob}	$V_{CB} = -10V, f = 1MHz$		0.9		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = -10mA, I_B = -1mA$	-0.04	-0.15		V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = -10mA, I_B = -1mA$	-0.82	-1.1		V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-15			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, R_{BE} = \infty$	-10			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
ON Resistance	R_{on}	$I_B = -3mA, f = 1MHz$		3.0		Ω

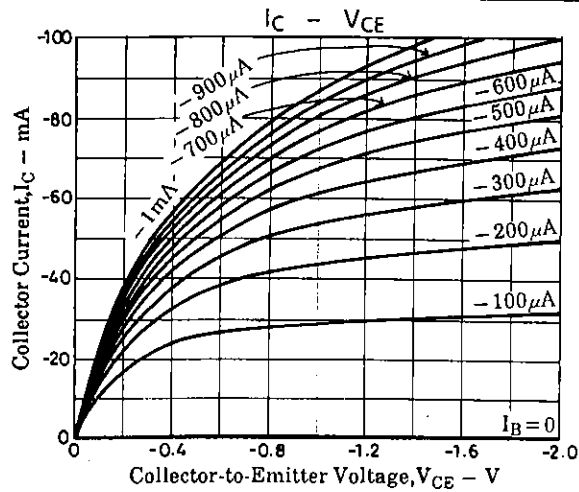
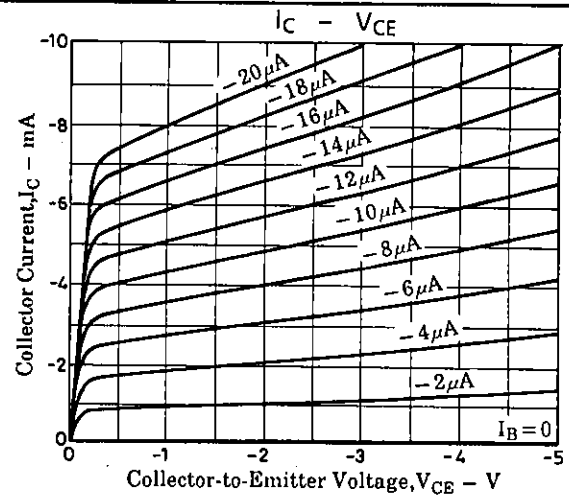
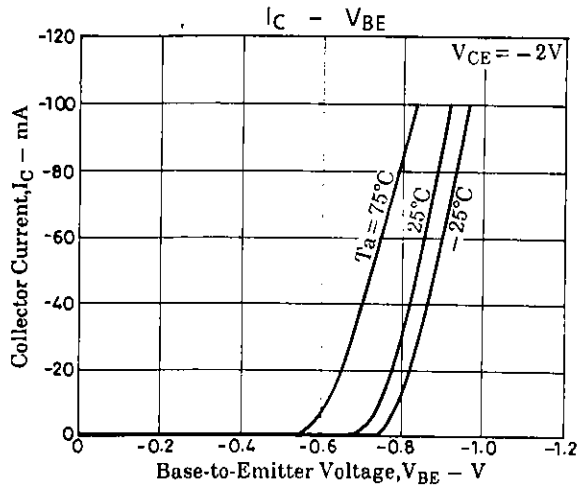
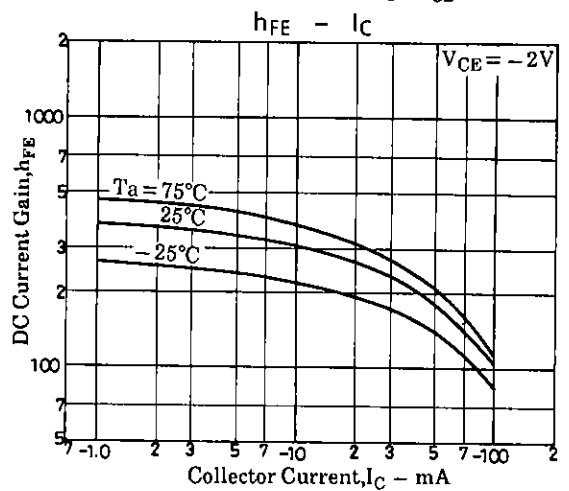
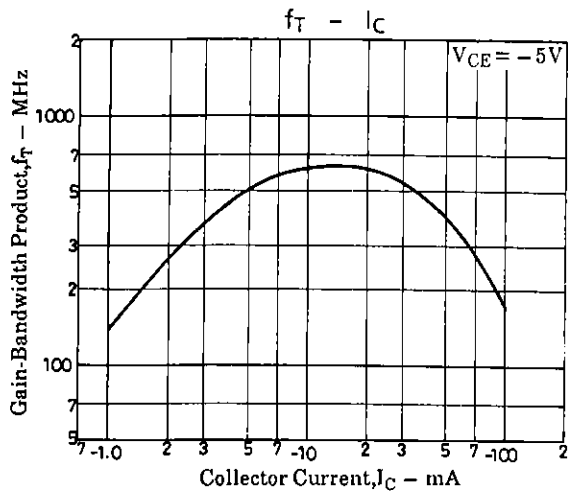
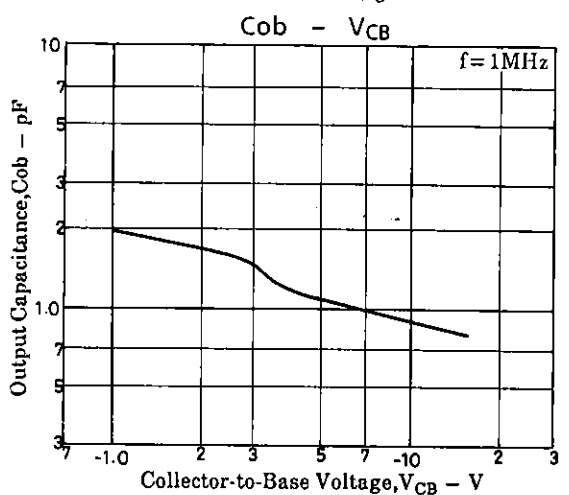
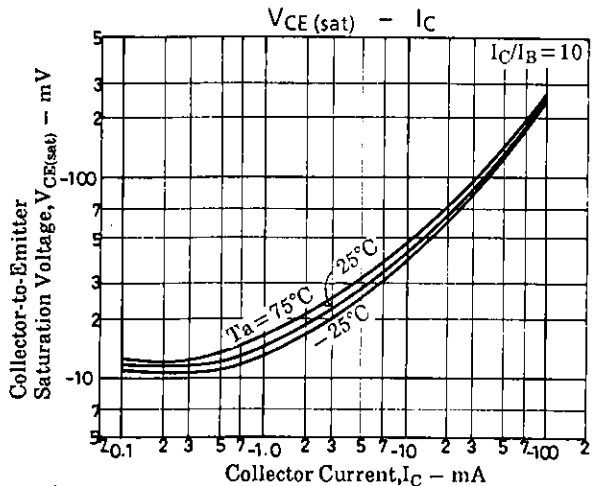
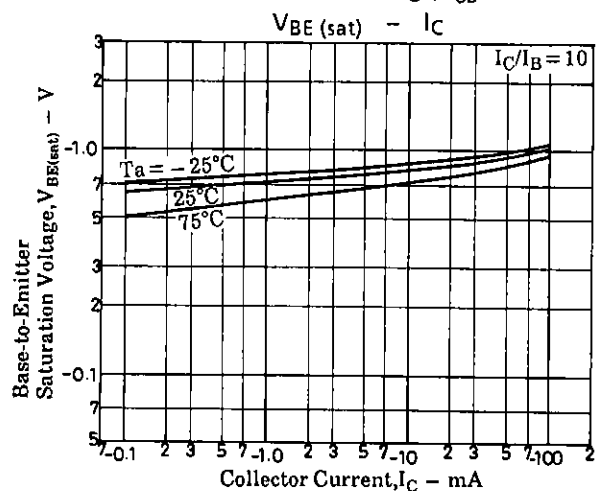
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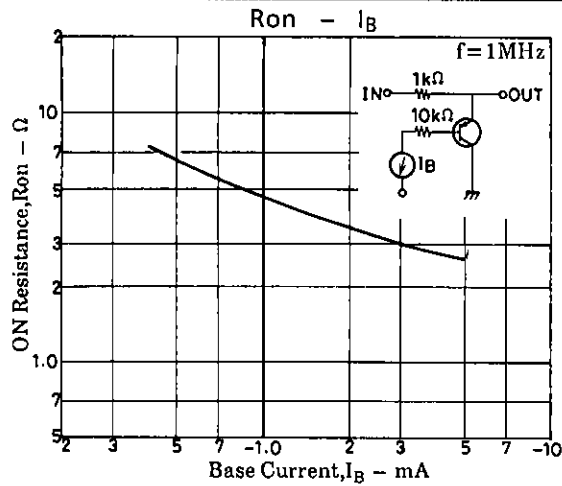
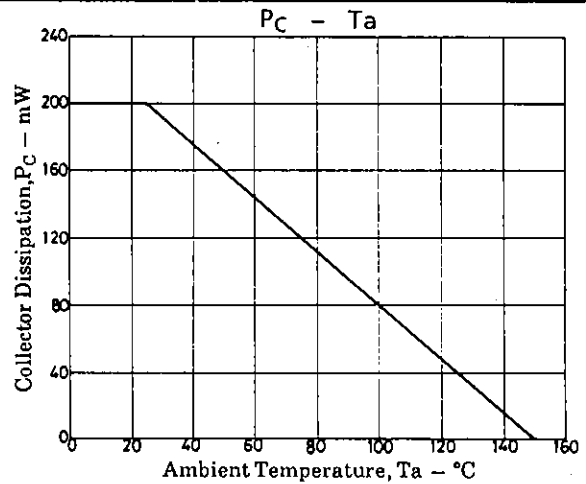
Package Dimensions 2059A

(unit: mm)

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